

The flexural modes of graphene on a substrate

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Out of plane vibrations are suppressed in graphene layers placed on a substrate. These modes, in suspended samples, are relevant for the understanding of properties such as the resistivity, the thermal expansion coefficient, and other. We present a general framework for the study of the properties of out of plane modes in graphene on different substrates. We use the model to estimate the substrate induced changes in the thermal expansion coefficient, or in the temperature dependence of the resistivity.

Introduction. Since its isolation in 2004 [1] graphene, a monolayer of carbon atoms arranged in a honeycomb lattice, has received great attention due to both its unique electrical and mechanical properties [2]. In graphene, the carbon atoms display an sp^2 hybridization, with the out of plane p_z orbitals forming a π band which is responsible for its electrical properties, while the sp^2 orbitals form strong σ in plane bonds that govern its mechanical properties. It has been verified both experimentally and theoretically [3–5] that graphene is the known material with the largest in plane elastic constants.

In freely suspended graphene samples the vibrations of the lattice can be classified into in plane and out of plane (flexural) modes, with the flexural modes lying at lower energies and showing a quadratic dispersion. Anharmonic effects at long wavelengths strongly couple in plane and flexural modes. The out of plane modes are responsible for the significant temperature dependence of the electronic resistivity at low temperatures [6–10]. Anharmonic effects in suspended graphene explain its negative thermal expansion coefficient, and they play a significant role in the thermal conductivity [11].

The interaction between a graphene layer and a substrate underneath change significantly the properties of the out of plane vibrations of the entire system [11, 12]. Coupling to a substrate also leads to heat transfer between the two systems [13–15].

We present here a simple but generic model which allows us to study the main properties of a graphene and substrate system in the long wavelength limit. We use the theory of elasticity, and describe the coupling between the graphene layer and the substrate by a simple function with a quadratic dependence on the separation. As an example we will present results for two of most used substrates: silicon dioxide, SiO_2 , and hexagonal boron nitride, hBN. We studied the thermal expansion of graphene on a substrate and also the effect of the flexural modes, modified by the coupling to the substrate, on the electrical resistivity.

The model. In our model the graphene membrane is supported by semi-infinite substrate that occupies the half-space $z < 0$. We will use continuum elasticity theory to model the system. We assume that only the out of

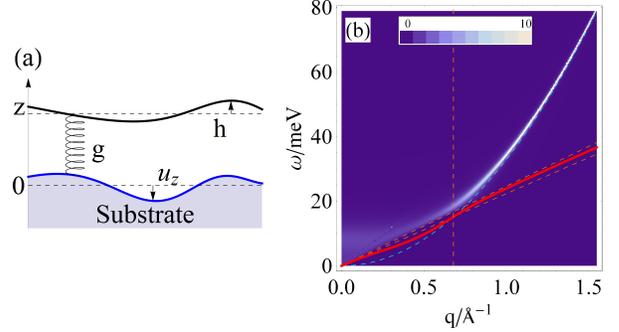


FIG. 1. (a) Pictorial representation of the model used for the membrane-substrate coupling. (b) Density plot of the spectral function $A(q, \omega)$ for graphene on SiO_2 measured in units of $\pi\omega_0^2/(2\gamma_0)$. The straight dashed lines represent from top to bottom: $\omega = c_T q$ and $\omega = c_R q$. The vertical line is at $q = c_R/\alpha$. The dashed parabola shows the flexural dispersion relation for a free membrane $\omega_f = \alpha q^2$. The solid red line, shows the dispersion relation of the hybridized flexural-Rayleigh mode, ω_{FR} .

plane displacements of the membrane couple to the out of plane displacements of the substrate as done in Ref. [13]. We will assume that the coupling is quadratic and neglect anharmonic effects. The action describing the system is given by $S = S_f + S_{\text{subs}} + S_{f\text{-subs}}$, with

$$\begin{aligned} S_f &= \int dt \int d^2\mathbf{x} \left(\frac{1}{2}\rho_{2D}\dot{h}^2 - \frac{1}{2}\kappa(\nabla^2 h)^2 \right), \\ S_{\text{subs}} &= \int dt \int d^2\mathbf{x} \int_{z<0} dz \left(\frac{1}{2}\rho_{3D}\dot{u}^2 - \frac{1}{2}\lambda_{ijkl}\partial_i u_j \partial_k u_l \right), \\ S_{f\text{-subs}} &= -\frac{g}{2} \int dt \int_{z=0} d^2\mathbf{x} (h - u_z)^2. \end{aligned} \quad (1)$$

S_f is the quadratic action for a free membrane, where h is the out of plane displacement field of the membrane, ρ_{2D} is the mass density per unit area and κ is the bending rigidity. From this action one obtains the well now quadratic dispersion relation for flexural phonons, $\omega_f(q) = \alpha q^2$, with $\alpha = \sqrt{\kappa/\rho_{2D}}$. For graphene we have $\rho_{2D} = 7.6 \times 10^{-7} \text{kg/m}^2$ and $\kappa \approx 1.1 \text{eV}$ [5]. S_{subs} is the action for an elastic medium occupying the half-space $z < 0$, with mass density per volume ρ_{3D} , constants given by

λ_{ijkl} and displacement field u_i . Finally, $S_{f\text{-subs}}$ describes the harmonic coupling between the out of plane displacement of the membrane and the out of plane displacement of the substrate surface, where g is a spring constant per unit area. We neglect here the shear between graphene and the substrate. Note that, if the substrate is not flat, such as SiO_2 , graphene will have regions that are strongly coupled to the substrate and will conform to its configuration, while other regions will become detached from it [16]. The detailed analysis of this situation is beyond the scope of the present paper, although the analysis presented below provides a reasonable approximation to the regions which are well attached to the substrate.

Assuming the dominant interaction is of Van der Waals type, g was estimated in Ref. [13] to have a value of $1.82 \times 10^{20} \text{J/m}^4$ for an SiO_2 substrate. In the absence of more rigorous calculations we will use this value both for SiO_2 and hBN substrates. The main object of interest from which all physically relevant quantities can be obtained is the height-height retarded correlation function:

$$D(q, \omega) = -\frac{i}{\hbar} \int dt d^2x \Theta(t) e^{i(\omega t - \mathbf{q} \cdot \mathbf{x})} \langle [h(x, t), h(0, 0)] \rangle, \quad (2)$$

where $\langle \rangle$ means thermal and quantum average. Since the theory is completely quadratic, it is possible to solve it exactly. As a matter of fact, the problem reduces to that of two coupled harmonic oscillators. Therefore one obtains

$$D(q, \omega) = \frac{1}{\rho_{2D} \omega^2 - \kappa q^4 - \Pi(q, \omega)}, \quad (3)$$

where $\Pi(q, \omega)$ is the correction to the free propagator due to coupling to the substrate,

$$\Pi(q, \omega) = \frac{g}{1 - g \Delta_0(q, \omega)}, \quad (4)$$

where $\Delta_0(q, \omega)$ is the surface-to-surface substrate propagator when $g = 0$:

$$\Delta_0(q, \omega) = -\frac{i}{\hbar} \int dt d^2x \Theta(t) e^{i(\omega t - \mathbf{q} \cdot \mathbf{x})} \langle [u_z(x, t), u_z(0, 0)] \rangle_0, \quad (5)$$

with both fields evaluated at the surface of the substrate, $z = 0$, and where the index $_0$ means that $g = 0$. In a quadratic theory, the quantum mechanical propagator is nothing more than the Green's function for the classical equations of motion. Therefore to obtain $\Delta_0(q, \omega)$ it suffices to study the classical elastic response of the substrate to an external pressure at the boundary $z = 0$. This analysis was done in Ref. [17] for the case of an isotropic elastic medium, such as amorphous SiO_2 , and the result for $\Delta_0(q, \omega)$ is given in the appendix for completeness. The generalization for the case of an uniaxial elastic substrate, such as hBN, will be provided somewhere else [18]. The important thing

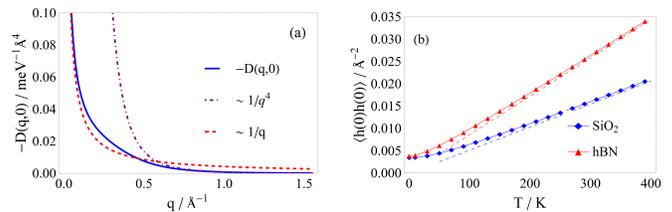


FIG. 2. (a) Plot of the static membrane propagator $D(q, 0)$ for a SiO_2 substrate. At high momentum we recover the $1/q^4$ behaviour of the free membrane, but at low momentum the behaviour is modified to $1/q$ due to coupling to the substrate. (b) Plot of $\langle h(0, 0)h(0, 0) \rangle$ as a function of temperature for SiO_2 and hBN substrates. As we can see the substrate has the effect of stabilizing the membrane.

to keep in mind, is that a semi-infinite elastic medium only supports modes that propagate into the bulk for $\omega > c_T q$, where $c_{T/L}$ is the transverse/longitudinal velocity (replace $c_T \rightarrow \sqrt{c_{44}/\rho_{3D}}$ for the uniaxial case). For $\omega < c_T q$, the substrate does not support bulk modes, supporting only a 2D surface Rayleigh mode with dispersion given by $\omega = c_R q$, where c_R is the velocity of the Rayleigh surface mode of the substrate. Substrate bulk modes will act as a dissipative bath, into which the flexural modes can decay, becoming broadened; while the Rayleigh mode will hybridize with the flexural mode without any broadening. Therefore the effect of coupling to the substrate on the flexural modes will be twofold: part of the spectral weight will hybridize with the Rayleigh mode (which has already pointed in Ref. [11]) having a dispersion relation approximately given by $\omega_{fR} \sim c_R q$ and which we will refer to as flexural-Rayleigh mode, fR; and part of the spectral weight will couple to the bulk modes of the substrate becoming gapped and broadened, with we will refer to as flexural-gapped, fG. This situation is illustrated in Fig. 1, where we show a density plot of the spectral function, $A(q, \omega) = -2\rho_{2D}\omega \text{Im}D(q, \omega)/\pi$ [19], along with the dispersion of the fR mode. The gap and broadening of the fG mode are controlled, respectively, by the quantities $\omega_0 = \sqrt{g/\rho_{2D}}$ and $\gamma_0 = g/(c_L \rho_{3D})$. To obtain the generalization to the uniaxial case replace $c_L \rightarrow \sqrt{c_{33}/\rho_{3D}}$. For the used value of g one obtains $\omega_0 \approx 10 \text{ meV}$ and $\gamma_0 \approx 13 \text{ THz}$ for graphene on SiO_2 and $\gamma_0 \approx 23 \text{ THz}$ for graphene on hBN. This values are an overestimation comparing with the inverse relaxation times obtained from molecular dynamics simulations for acoustic flexural phonons on a SiO_2 substrate, $1/\tau \sim 0.1 - 1 \text{ THz}$ [12]. The hybridization between flexural and Rayleigh modes is strongest for $q < c_R/\alpha$, being more relevant for values of the spring constant g such that $\omega_0 \sim c_R^2/(2\alpha)$.

Results. Having obtained the propagator, $D(q, \omega)$, one can compute all physically interesting quantities. To study the ordering of the membrane one can look for instance at the same-time height-height correlation func-

tion:

$$\langle h(x, 0)h(0, 0) \rangle = -\hbar \int \frac{d^2 q d\omega}{(2\pi)^3} e^{i\mathbf{q}\cdot\mathbf{x}} \coth\left(\frac{\hbar\omega}{2k_B T}\right) \text{Im}D(q, \omega), \quad (6)$$

which reduces in the high temperature limit to $\langle h(x, 0)h(0, 0) \rangle \simeq -k_B T \int \frac{d^2 q}{(2\pi)^2} e^{i\mathbf{q}\cdot\mathbf{x}} D(q, 0)$, in accordance with the equipartition theorem. For the quadratic dispersion relation of flexural phonons it is known that the same point correlation function, $\langle h(0, 0)h(0, 0) \rangle$, diverges at any finite temperature, indicating that there should be no crystalline order. As expected, the coupling to a substrate stabilizes the membrane. In Fig. 2 we can see a plot of $\langle h(0, 0)h(0, 0) \rangle$ and of $D(q, 0)$. It is interesting to notice that contrary to what one would naively think $D(q, 0)$ does not tend to a constant for small q but instead goes as $1/q$. This is because the surface substrate propagator at zero frequency and small momentum behaves as $\Delta_0(q, 0) = -1/(K_1 q)$ (with $K_1 = 2\rho_{3D}c_T^2 (c_L^2 - c_T^2)/c_L^2$ for an isotropic medium) dominating $D(q, 0)$. This behaviour will make all the results for physical quantities finite, without the need to impose any infrared cutoff due to anharmonic effects or finite sample size. For large distances the height-height correlation function now behaves as $\langle h(x, 0)h(0, 0) \rangle \simeq k_B T/(2\pi K_1 x)$, a result that is independent of g and coincides with the one for $\langle u_z(x, 0)u_z(0, 0) \rangle_0$ at $z = 0$. An-

other quantity that is also interesting to look at and that is of greater experimental importance is the areal thermal expansion coefficient of graphene, α_A , on a substrate. Generalizing the quasi-harmonic treatment of coupling between flexural and stretching modes of a membrane of Ref. [20] for the case of flexural phonons modified by interactions one obtains

$$\alpha_A = \frac{\hbar}{k_B T^2} \int \frac{d^2 q d\omega}{(2\pi)^3} q^2 \omega \frac{\text{Im}D(q, \omega)}{4 \sinh^2\left(\frac{\hbar\omega}{2k_B T}\right)}. \quad (7)$$

The obtained value is negative since $\text{sgn}(\text{Im}D(q, \omega)) = -\text{sgn}(\omega)$ and tends to a constant in the high temperature limit. Close to room temperature one obtains a value in the order of -6 to $-7 \times 10^{-6} \text{ K}^{-1}$ a value that is smaller in absolute value than the one obtained for a suspended membrane [20] as expected. Finally, knowing the form of the propagator $D(q, \omega)$ one can also study the contribution to the electrical resistivity from flexural phonons on supported graphene. Generalizing the results from Ref. [8, 9] we compute the resistivity from the known formula $\rho^{-1} = \frac{e^2}{2} \mathcal{N}(\epsilon_F) v_F^2 \tau_F^{tr}$, where $\mathcal{N}(\epsilon_F) = 2k_F/(\pi \hbar v_F)$ is graphene density of states at the Fermi level, with v_F and k_F the Fermi velocity and momentum respectively, and τ_F^{tr} the transport scattering time. In the quasi-elastic approximation, one obtains

$$\frac{1}{\tau_F^{tr}} = \frac{\pi}{\hbar} \int \frac{d^2 q d^2 p}{(2\pi)^4} \int \frac{d\omega d\nu}{\pi^2} \hbar^2 |w_{k_F, q, p}|^2 (1 - \cos \theta_{k_F, k_F+q+p}) d(\omega, \nu) \delta(\epsilon_{k+q+p} - \epsilon_F) \text{Im}D(p, \nu) \text{Im}D(q, \omega), \quad (8)$$

where $|w_{k, q, p}|^2 = q^2 p^2 \mathcal{D}^2(|\mathbf{q} + \mathbf{p}|)$ is the squared electron-flexural phonon coupling, with $\mathcal{D}^2(Q) = D^2(Q) \sqrt{1 - \left(\frac{Q}{2k_F}\right)^2} + \frac{\hbar^2 v_F^2 \beta^2}{8a^2}$ the generalized deformation potential [8] that takes into account coupling via screened deformation potential and bond stretching vector potential [2, 21–23], where $D(Q)$ is the screened deformation potential and $\beta = -\frac{d \log t}{d \log a}$ describes the change in electron hopping with bond stretching. We have defined the function due to thermal occupation factors:

$$d(\omega, \nu) = \frac{1}{4 \cosh\left(\frac{\hbar(\omega+\nu)}{2k_B T}\right) \sinh\left(\frac{\hbar\omega}{2k_B T}\right) \sinh\left(\frac{\hbar\nu}{2k_B T}\right)}. \quad (9)$$

We use a value of $D_0 \approx 25 \text{ eV}$ for the unscreened deformation potential and $\beta \approx 2.5$ for the bond stretching parameter. The electron scattering due to flexural phonons is a two phonon process. Therefore there are three contributions: (i) scattering by two fG modes, (ii) scattering by two fR modes, and (iii) a mixed process involving scattering by one fR mode and one fG mode. In Fig. 4 we plot

of the resistivity due to flexural phonons on supported graphene on SiO_2 and hBN, also showing the individual contribution of scattering by two fR modes. We see that the contribution from fR modes is smaller in hBN than in SiO_2 . This is explained by the smaller hybridization with the Rayleigh mode in hBN due to a smaller Rayleigh velocity when compared to SiO_2 . Nevertheless we see that at room temperature the obtained resistivities are of order $\sim 1\Omega$ much smaller than the expected contribution from flexural modes in suspended samples [8] and the contribution from in plane phonons [9, 24].

Conclusions. We have employed a simple model to do a complete study of the dynamics of flexural modes of a membrane coupled to a substrate, with the aim of understanding the role that this modified modes might have in the physics of graphene. Since a half-space elastic medium supports both 3D bulk modes and a 2D surface Rayleigh mode, coupling of the membrane modes to the substrate will lead to a splitting of the spectral weight of the flexural modes in two parts: one that will hybridize with the substrate Rayleigh mode acquiring an almost

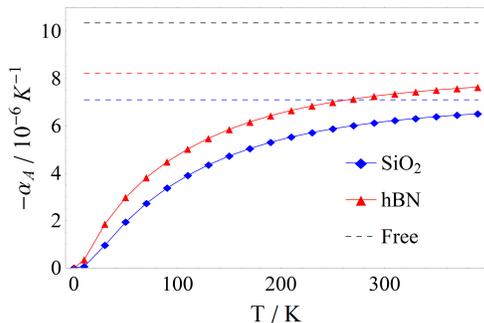


FIG. 3. Areal thermal expansion coefficient as a function of temperature for a graphene membrane supported by SiO₂ and hBN substrates, solid line, and its high temperature limits, dashed line. It is also show the expected value of the areal thermal expansion at high temperature for a free membrane imposing an infrared cutoff due to anharmonic effects [20]

linear dispersion relation for momentum $q \lesssim c_R/\alpha$, while the other part will become gapped and broadened due to coupling to the bulk modes. As expected coupling to the substrate leads to a stabilization of the membrane and all correlation functions becomes finite, while for a free membrane they are known to have infrared divergences in the harmonic theory. It is worthwhile noticing that at high temperature the low momentum behavior of the height-height correlation function changes from $1/q^4$ to $1/q$. This implies that for large distances the height-height function will go as $1/x$. We also explored the behavior of the areal thermal expansion coefficient of graphene on substrate. At room temperature we obtained a value of the order of -6 to $-7 \times 10^{-6} \text{ K}^{-1}$. Finally we studied the contribution of flexural modes on the electrical resistivity of graphene supported by a substrate. We found that coupling to the membrane strongly suppresses the contribution of the flexural phonons, even if one takes into account the contribution coming from the hybridized flexural-Rayleigh mode. Note that the model describes a flat graphene layer on a flat surface. This is a good approximation for substrates such as hBN. In the case of corrugated substrates, such as SiO₂, our analysis is expected to describe the regions where the graphene layer and the substrate are flat and the two systems are in close contact.

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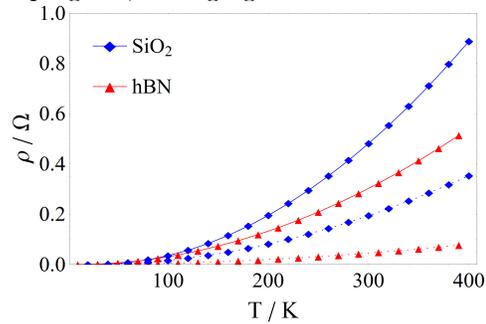


FIG. 4. Computed contribution to the resistivity due to flexural phonons on supported graphene on SiO₂ and hBN substrates for a electronic density $n = 10^{12} \text{ cm}^{-2}$. The dotted lines show the contribution from the scattering involving two fR phonons.

	SiO ₂		hBN
ρ (kg/m ³)	2200	ρ (kg/m ³)	2280
	$\times 10^9 \text{ Pa}$		$\times 10^9 \text{ Pa}$
$\lambda + 2\mu$	78	c_{11}	811
μ	31	c_{12}	169
$c_{11} = c_{33} = \lambda + 2\mu$		c_{13}	0
$c_{12} = c_{13} = \lambda$		c_{33}	27.0
$c_{44} = \mu$		c_{44}	7.7
c_R (m/s)	3392	c_R (m/s)	1835

TABLE I. Elastic properties for amorphous SiO₂ and hBN. Data for hBN taken from Ref. [25].

Substrate surface-to-surface propagator

The response to an external pressure $\sigma_z^{(ext)}$ at the boundary, $z = 0$, of an elastic medium occupying the half-space $z < 0$ is described by

$$u_z(q, \omega) = -\Delta_0(q, \omega) \sigma_z^{(ext)}(q, \omega), \quad (\text{A.10})$$

where q is the in plane momentum and $u_z(q, \omega)$ is evaluated at $z = 0$. The response function, $\Delta_0(q, \omega)$, which coincides with the quantum mechanical propagator (5) for an isotropic substrate is given by [17]:

$$\Delta_0(q, \omega) = -\text{sign}(\omega) \frac{i\omega^2}{c_T^4 S(q, \omega)} \sqrt{\left(\frac{\omega}{c_T}\right)^2 - q^2 + \text{sgn}(\omega)i0^+}, \quad (\text{A.11})$$

with

$$S(q, \omega) = \left(\left(\frac{\omega}{c_t} \right)^2 - 2q^2 \right)^2 + 4q^2 \sqrt{\left(\frac{\omega}{c_T} \right)^2 - q^2 + \text{sgn}(\omega)i0^+} \sqrt{\left(\frac{\omega}{c_L} \right)^2 - q^2 + \text{sgn}(\omega)i0^+}. \quad (\text{A.12})$$

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